



DUAL DIFFERENTIAL AMPS (Cont.)

NPN Transistors

Type No.	Case Style	V _{CBO} (V) Min	V _{CEO} (V) Min	V _{EBO} (V) Min	I _{CBO} (nA) Max	V _{CB} (V)	h _{FE} @ I _C			h _{FE1} (%) Max	V _{BE1} -V _{BE2} (mV) Max	ΔV _{BE1} -V _{BE2} ΔT (μV/°C) Max	C _{ob} (pF) Max	f _T (MHz) Min Max	NF (dB) Max	Test Condition	Process No.
2N2978	TO-71	60	60	6	2	45	60 100 150	240 0.1 1	0.01	10	5 3 5	10	6	60	4 4	3 2	07
2N2979	TO-71	60	60	6	2	45	150 225 300	600 0.1 1	0.01	10	5 3 5	10	6	60	3 3	3 2	07
2N3587	TO-78	60	45	5	10	40	50 80	0.1 500	1	†20	20	20	8	80 200	10	3	07
2N3680	TO-78	60	50	6	10	45	150 225 300	600 0.1 1	0.01	10	3	5	6	60 180	3	2	07
2N3907	TO-78	60	45	6	10	45	60 70 120	300 500 1	0.01	10	2 1 2.5	5	6	60 240	4	3	07
2N3908	TO-78	60	60	6	2	45	100 125 200	500 800 1	0.01	10	2 1 2.5	5	6	60 240	3	3	07
ND5700	TO-78	45	45	6	0.2	50	200 200 200	1500 2000 5	0.01	5	0.5	2	3		3	5	570
ND5701	TO-78	45	45	6	0.2	50	200 200 200	1500 2000 5	0.01	10	1	5	3		3	5	570
ND5702	TO-78	45	45	6	0.2	50	200 200 200	1500 2000 5	0.01	10	2	10	3		3	5	570

Test Conditions:

1. I_C = 10 μA, V_{CE} = 5V,
R_G = 10 kΩ, f = 1 kHz

2. I_C = 10 μA, V_{CE} = 5V,
R_G = 10 kΩ, BW = 15.7 kHz

3. I_C = 10 μA, V_{CE} = 5V,
R_G = 10 kΩ, f = 1 kHz
BW = 200 Hz

4. I_C = 10 μA, V_{CE} = 5V,
R_G = 10 kΩ, f = 100 Hz

5. I_C = 100 μA, V_{CE} = 5V,
R_G = 10 kΩ, BW = 15.7 kHz

*This parameter measured at frequency = 1 kHz.
†T_A = -55°C to +125°C.